

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claim 1 (previously presented): A transistor comprising:
a source electrode and a drain electrode arranged in mutually opposing relation;
a semiconductor film comprising at least one layer disposed between the source electrode and the drain electrode;
a gate electrode disposed in adjacent relation to the semiconductor film; and
a gate insulating film disposed between the gate electrode and each of the source electrode, the drain electrode, and the semiconductor film, wherein
a concentration of fluorine contained in the gate insulating film is 1×10^{20} atoms/cm³ or less;
the transistor is of an inverted stagger type in which the gate insulating film and the semiconductor film are formed in that order and the semiconductor film is disposed on the gate insulating film; and
the gate insulating film is an amorphous silicon nitride film.

Claim 2 (original): The transistor of claim 1, wherein the concentration of the contained fluorine is 1×10^{19} atoms/cm³ or less.

Claim 3 (original): The transistor of claim 1, which is of a field-effect type.

Claim 4 (canceled).

Claim 5 (original): The transistor of claim 1, wherein the gate insulating film is deposited by a CVD method.

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Claims 6 and 7 (canceled).

Claim 8 (previously presented): A liquid crystal display device comprising the transistor of claim 1 as a switching element for a pixel electrode portion.